

AMENDMENTS TO THE SPECIFICATION:

Please amend the paragraph beginning at page 3, line 13, as follows:

To achieve the above-described object, the present invention is an on-wafer monitoring system capable of measuring the operation of the plasma treatment device on wafer, which comprises one or a plurality of sensor sections, a power source unit, and an I/O unit that inputs/outputs signals from/to outside, which are provided on a silicon substrate, in which the sensor sections have pattern portions, and a plurality of electrodes for separating ions and electrons of plasma by energy, and electrodes having the same potential as that of the silicon substrate directly under the pattern portions, in which the power source unit can be constituted such that power is taken out from plasma potential or power is taken out from photoelectromotive force of a PLZT device.

HAYES SOLOWAY P.C.
130 W. CUSHING STREET
TUCSON, AZ 85701
TEL. 520.882.7623
FAX. 520.882.7643

175 CANAL STREET
MANCHESTER, NH 03101
TEL. 603.668.1400
FAX. 603.668.8567